

LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for imaging a semiconductor wafer during formation of an integrated circuit on the semiconductor wafer, the method comprising ~~the steps of~~:

preparing a mask that is formed with at least first and second mask patterns thereon for forming the integrated circuit on the semiconductor wafer, the first mask pattern being different in configuration from the second mask pattern;

positioning the mask on an exposure system;

positioning the wafer on the exposure system;

forming a first image, which corresponds to the first mask pattern, on the wafer by projecting light through the mask onto the wafer;

removing the wafer from the exposure system;

subjecting the wafer to subsequent integrated circuit forming steps;

repositioning the wafer on the exposure system; and

forming a second image, which corresponds to the second mask pattern, on the wafer by projecting light through the mask onto the wafer.

2. (Currently Amended) A method for forming an integrated circuit on a semiconductor wafer, the method comprising ~~the steps of~~:

(a) preparing a mask that is formed with a plurality of mask patterns thereon for forming the integrated circuit on the semiconductor wafer, the first mask pattern being different in configuration from the second mask pattern;

(b) positioning the mask on an exposure system;

(c) positioning the wafer on the exposure system;

(d) forming an image, which corresponds to one of the mask patterns, on the wafer by projecting light through the mask onto the wafer;

(e) removing the wafer from the exposure system;

- (f) subjecting the wafer to subsequent integrated circuit forming steps so as to form a layer of the integrated circuit on the semiconductor wafer;
- (g) repositioning the wafer on the exposure system;
- (h) forming another image, which corresponds to another one of the mask patterns, on the wafer by projecting light through the mask onto the wafer;
- (i) removing the wafer from the exposure system;
- (j) subjecting the wafer to further integrated circuit forming steps so as to form another layer of the integrated circuit on the layer of the integrated circuit previously formed on the wafer; and
- (i) repeating the steps from (g) to (j) so as to form other layers of the integrated circuit on the wafer.

3. (Currently Amended) The method of Claim 2, wherein the integrated circuit forming steps include at least one of photoresist developing, photoresist baking, photoresist removing, [[or]] photoresist etching, photoresist depositing, [[and]] or doping.

4. (Original) The method of Claim 3, wherein the mask is a binary mask.

5. (Original) The method of Claim 3, wherein the mask is a phase shift mask.

6. (Currently Amended) A method for forming an integrated circuit on a semiconductor wafer, the method comprising the steps of:

- (a) preparing a mask that is formed with a plurality of mask patterns thereon for forming the integrated circuit on the semiconductor wafer, the first mask pattern being different in configuration from the second mask pattern;
- (b) positioning the mask on an exposure system;
- (c) positioning the wafer on the exposure system;
- (d) forming an image, which corresponds to one of the mask patterns, on the wafer by projecting light through the mask onto the wafer;
- (e) removing the wafer from the exposure system;

- (f) subjecting the wafer to subsequent integrated circuit forming steps so as to form a portion of a layer of the integrated circuit on the semiconductor wafer;
- (g) repositioning the wafer on the exposure system;
- (h) forming another image, which corresponds to another one of the mask patterns, on the wafer by projecting light through the mask onto the wafer;
- (i) removing the wafer from the exposure system; and
- (j) subjecting the wafer to integrated circuit forming steps so as to form another portion of the layer of the integrated circuit.